**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Trench MOSFET technology
- · Logic-level compatible
- · Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

## 3. Applications

- · Relay driver
- High-speed line driver
- · Low-side loadswitch
- · Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions  |     | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|-----|-----|------|
| $V_{DS}$          | drain-source voltage             | T <sub>j</sub> = 25 °C  |     | -   | -   | 60  | V    |
| $V_{GS}$          | gate-source voltage              |   |     | -20 | -   | 20  | V    |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s         | [1] | -   | -   | 3.1 | Α    |
| Static characte   | Static characteristics           |   |     |     |     |     |      |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 2.4 \text{ A}; T_j = 25 \text{ °C}$ |     | -   | 96  | 123 | mΩ   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

### **Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1   | D      | drain       | <u> </u>           | D              |
| 2   | D      | drain       |                    |                |
| 3   | G      | gate        | 0<br>1 1 2 1 3     | G $+$ $+$ $+$  |
| 4   | S      | source      | TSOP6 (SOT457)     |                |
| 5   | D      | drain       |                    |                |
| 6   | D      | drain       |                    | S<br>017aaa255 |

# 6. Ordering information

### **Table 3. Ordering information**

| Type number | Package | je   |         |  |  |  |  |
|-------------|---------|--|---------|--|--|--|--|
|             | Name    | Description                                      | Version |  |  |  |  |
| PMN120ENE   | TSOP6   | plastic surface-mounted package (TSOP6); 6 leads | SOT457  |  |  |  |  |

# 7. Marking

### **Table 4. Marking codes**

| Type number | Marking code |
|-------------|--------------|
| PMN120ENE   | 3K           |

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## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions  |     | Min | Max  | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| $V_{DS}$         | drain-source voltage    | T <sub>j</sub> = 25 °C                                    |     | -   | 60   | V    |
| $V_{GS}$         | gate-source voltage     |   |     | -20 | 20   | V    |
| I <sub>D</sub>   | drain current           | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s | [1] | -   | 3.1  | Α    |
|                  |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C          | [1] | -   | 2.4  | Α    |
|                  |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C         | [1] | -   | 1.5  | Α    |
| I <sub>DM</sub>  | peak drain current      | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$       |     | -   | 10   | Α    |
| P <sub>tot</sub> | total power dissipation | T <sub>amb</sub> = 25 °C                                  | [2] | -   | 570  | mW   |
|                  |                         |   | [1] | -   | 1.4  | W    |
|                  |                         | T <sub>sp</sub> = 25 °C                                   |     | -   | 6.25 | W    |
| T <sub>j</sub>   | junction temperature    |   |     | -55 | 150  | °C   |
| T <sub>amb</sub> | ambient temperature     |   |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature     |   |     | -65 | 150  | °C   |
| Source-drain di  | ode                     |   |     | •   |      |      |
| I <sub>S</sub>   | source current          | T <sub>amb</sub> = 25 °C                                  | [1] | -   | 1.4  | Α    |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

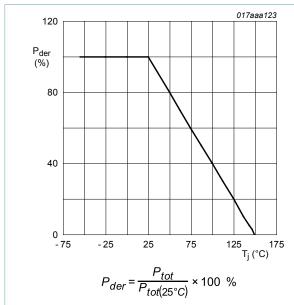


Fig. 1. Normalized total power dissipation as a function of junction temperature

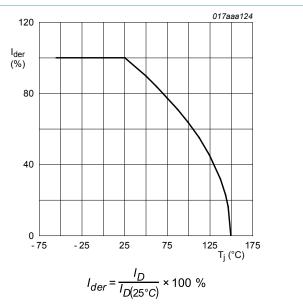


Fig. 2. Normalized continuous drain current as a function of junction temperature

#### 60 V, N-channel Trench MOSFET

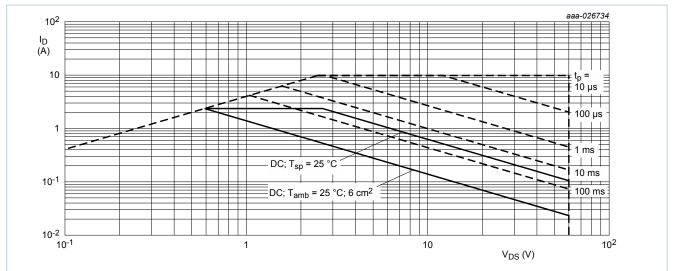


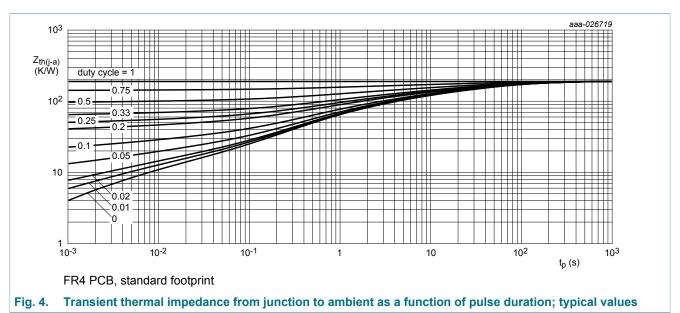
Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

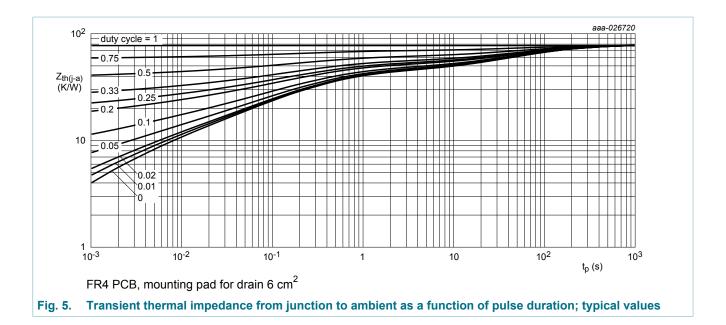
| Symbol                | Parameter  | Conditions |     | Min | Тур | Max | Unit |
|-----------------------|--|------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub>  | thermal resistance from junction to ambient            |            | [1] | -   | 190 | 220 | K/W  |
|                       |  |            | [2] | -   | 78  | 90  | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance<br>from junction to solder<br>point |            |     | -   | 15  | 20  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>



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### 10. Characteristics

#### **Table 7. Characteristics**

| Symbol               | Parameter                         | Conditions   | Min | Тур  | Max | Unit |
|----------------------|-----------------------------------|--|-----|------|-----|------|
| Static chara         |                                   |  |     | - 71 |     |      |
| V <sub>(BR)DSS</sub> | drain-source<br>breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$                                       | 60  | -    | -   | V    |
| V <sub>GSth</sub>    | gate-source threshold voltage     | I <sub>D</sub> = 250 μA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C | 1.3 | 1.7  | 2.7 | V    |
| I <sub>DSS</sub>     | drain leakage current             | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C              | -   | -    | 1   | μA   |
| I <sub>GSS</sub>     | gate leakage current              | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$           | -   | -    | 10  | μA   |
|                      |                                   | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C             | -   | -    | -10 | μA   |
|                      |                                   | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C              | -   | -    | 1   | μA   |
|                      |                                   | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C             | -   | -    | -1  | μA   |
| Doon                 | drain-source on-state             | $V_{GS}$ = 10 V; $I_D$ = 2.4 A; $T_j$ = 25 °C                                      | -   | 96   | 123 | mΩ   |
|                      | resistance                        | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 2.4 A; T <sub>j</sub> = 150 °C            | -   | 192  | 246 | mΩ   |
|                      |                                   | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 2.2 A; T <sub>j</sub> = 25 °C            | -   | 108  | 146 | mΩ   |
| g <sub>fs</sub>      | forward transconductance          | $V_{DS}$ = 10 V; $I_D$ = 0.9 A; $T_j$ = 25 °C                                      | -   | 10.2 | -   | S    |
| $R_G$                | gate resistance                   | f = 1 MHz  | -   | 10   | -   | Ω    |
| Dynamic ch           | naracteristics                    |  |     |      |     |      |
| Q <sub>G(tot)</sub>  | total gate charge                 | $V_{DS}$ = 30 V; $I_{D}$ = 2.1 A; $V_{GS}$ = 10 V;                                 | -   | 5.9  | 7.4 | nC   |
| Q <sub>GS</sub>      | gate-source charge                | T <sub>j</sub> = 25 °C   | -   | 0.6  | -   | nC   |
| $Q_{GD}$             | gate-drain charge                 |  | -   | 1.1  | -   | nC   |
| C <sub>iss</sub>     | input capacitance                 | V <sub>DS</sub> = 30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                          | -   | 275  | -   | pF   |
| C <sub>oss</sub>     | output capacitance                | T <sub>j</sub> = 25 °C   | -   | 24   | -   | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance      |  | -   | 17   | -   | pF   |
| t <sub>d(on)</sub>   | turn-on delay time                | $V_{DS} = 30 \text{ V}; I_D = 2.1 \text{ A}; V_{GS} = 10 \text{ V};$               | -   | 6    | -   | ns   |
| t <sub>r</sub>       | rise time                         | $R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$  | -   | 9    | -   | ns   |
| t <sub>d(off)</sub>  | turn-off delay time               | _  | -   | 16   | -   | ns   |
| t <sub>f</sub>       | fall time                         |  | -   | 6    | -   | ns   |
| Source-dra           | in diode                          |  | '   |      |     | ,    |
| $V_{SD}$             | source-drain voltage              | I <sub>S</sub> = 1.4 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C              | _   | 0.8  | 1.2 | V    |

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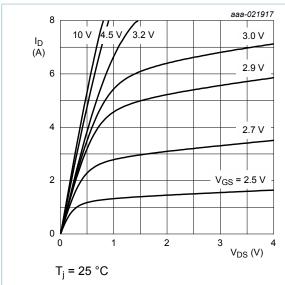


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

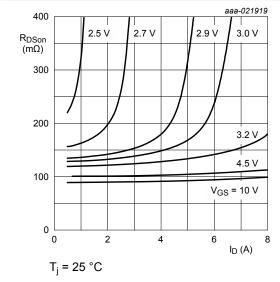


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

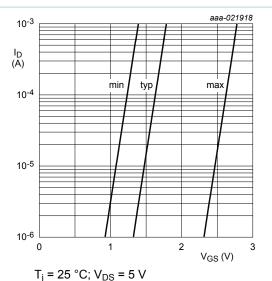


Fig. 7. Sub-threshold drain current as a function of

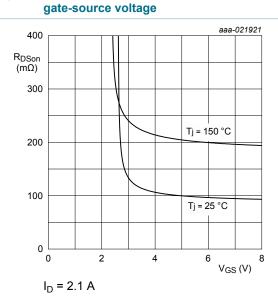


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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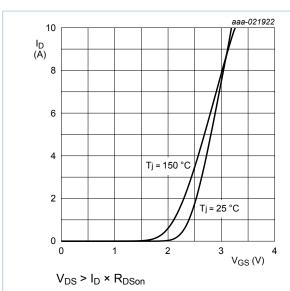


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

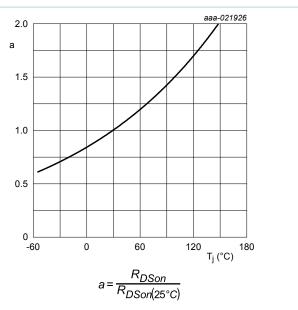


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

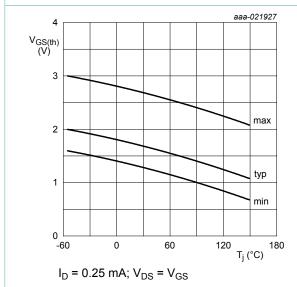


Fig. 12. Gate-source threshold voltage as a function of junction temperature

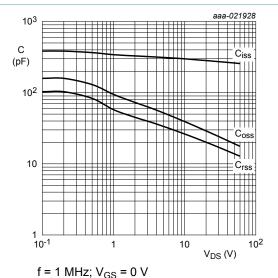


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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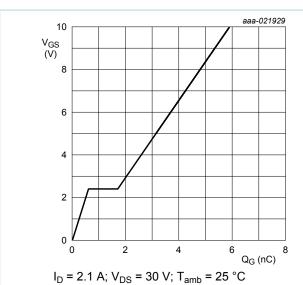


Fig. 14. Gate-source voltage as a function of gate charge; typical values

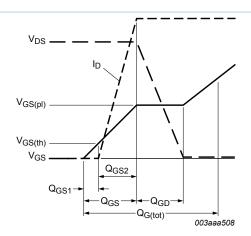


Fig. 15. Gate charge waveform definitions

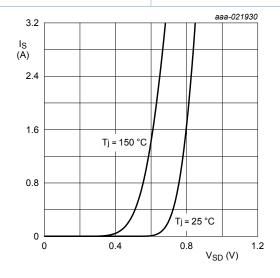


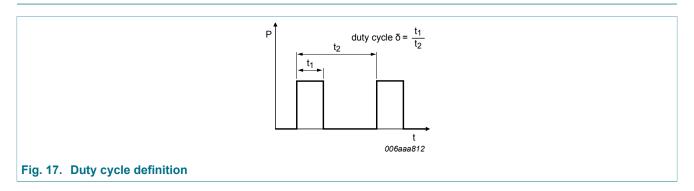
Fig. 16. Source current as a function of source-drain voltage; typical values

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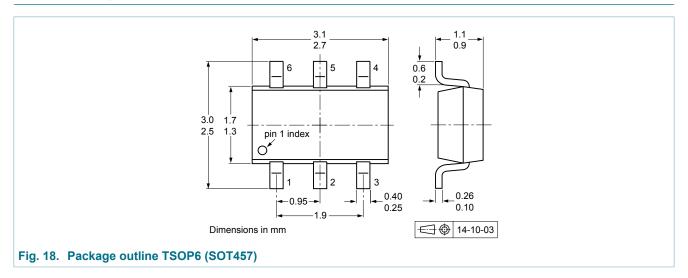
 $V_{GS} = 0 V$ 

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### 11. Test information

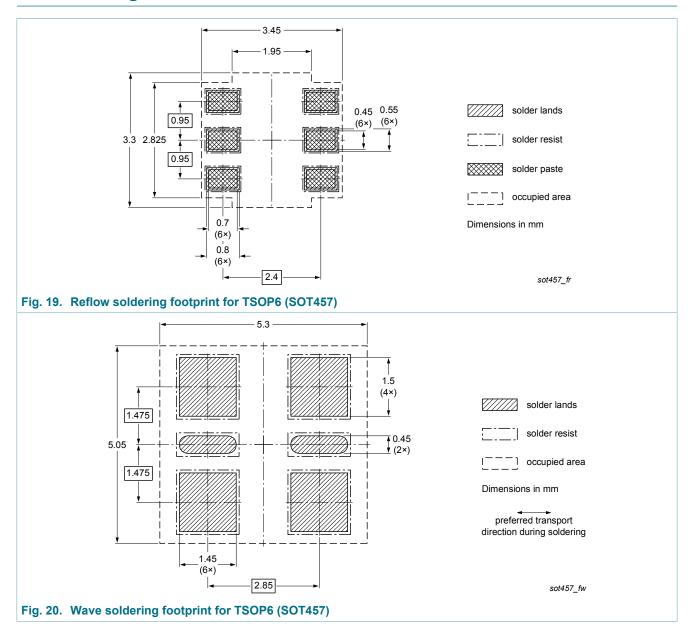


# 12. Package outline



60 V, N-channel Trench MOSFET

## 13. Soldering



**60 V, N-channel Trench MOSFET** 

# 14. Revision history

#### Table 8. Revision history

|                | . )  |                    |               |               |  |  |  |
|----------------|--|--------------------|---------------|---------------|--|--|--|
| Data sheet ID  | Release date   | Data sheet status  | Change notice | Supersedes    |  |  |  |
| PMN120ENE v.2  | 20171214   | Product data sheet | -             | PMN120ENE v.1 |  |  |  |
| Modifications: | Characteristics, temperature condition removed from gate resistance. |                    |               |               |  |  |  |
| PMN120ENE v.1  | 20171127   | Product data sheet | -             | -             |  |  |  |

#### 60 V, N-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary<br>[short] data<br>sheet | Qualification      | This document contains data from the preliminary specification.                       |
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